N-Channel Enhancement Mode Field Effect Transistor

Product Summary

● V_{DS}	100V
● I_D	70A
● $R_{DS(ON)}$(at V_{GS}=10V)	8.6 mohm
● $R_{DS(ON)}$(at V_{GS}=6V)	13 mohm
● 100% EAS Tested	
● 100% V_{DS} Tested	

General Description

- Low $R_{DS(on)}$ & FOM
- Extremely low switching loss
- Excellent stability and uniformity
- Fast switching and soft recovery
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- Power switching application
- Hard switched and high frequency circuits
- UPS

■ Absolute Maximum Ratings (T$_A$=25 unless otherwise noted)

Parameter	

Typical Performance Characteristics

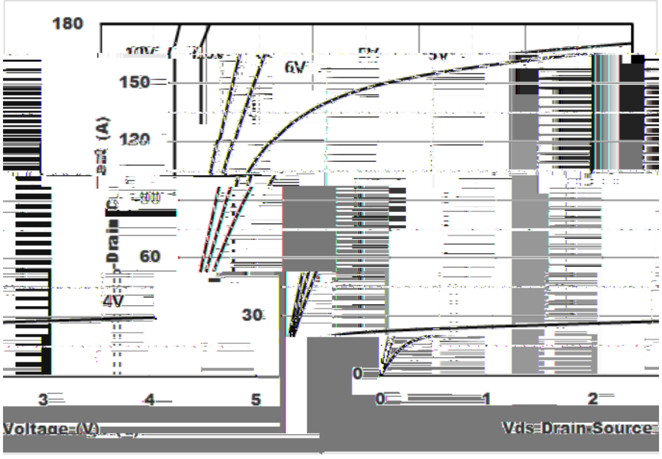


Figure1. Output Characteristics

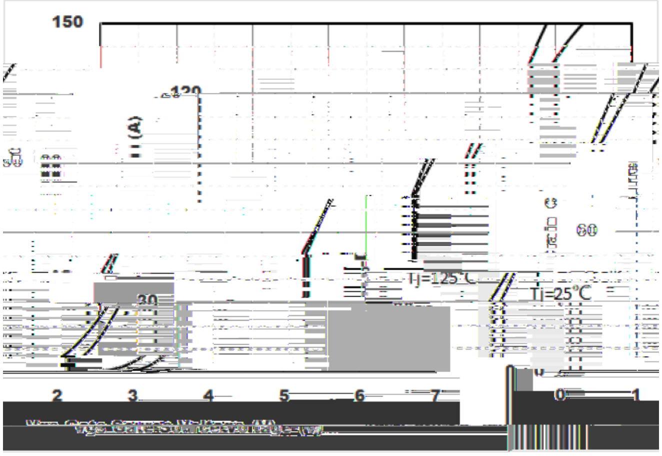


Figure2. Transfer Characteristics

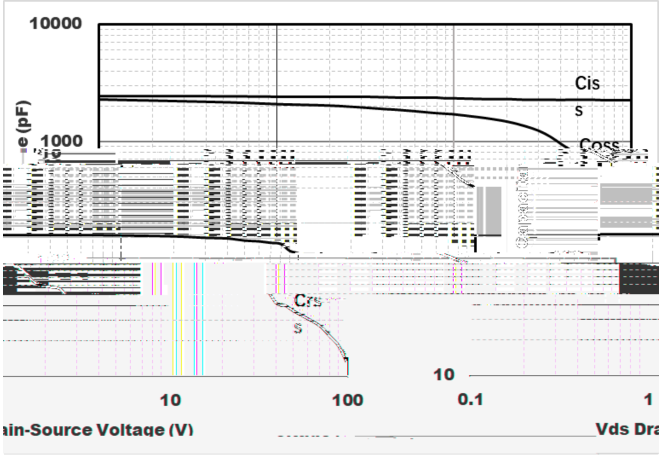


Figure3. Capacitance Characteristics

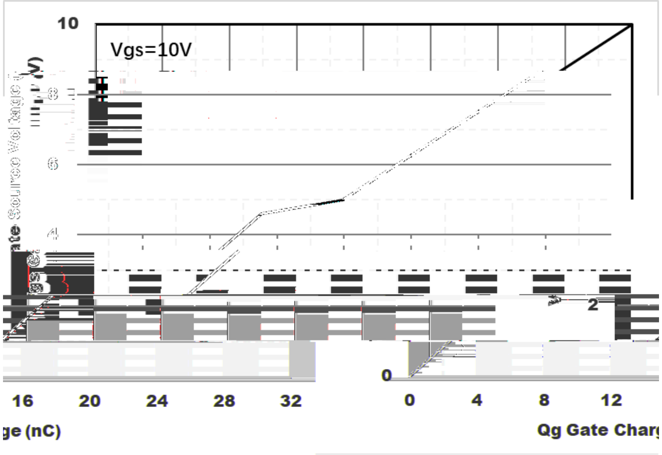


Figure4. Gate Charge

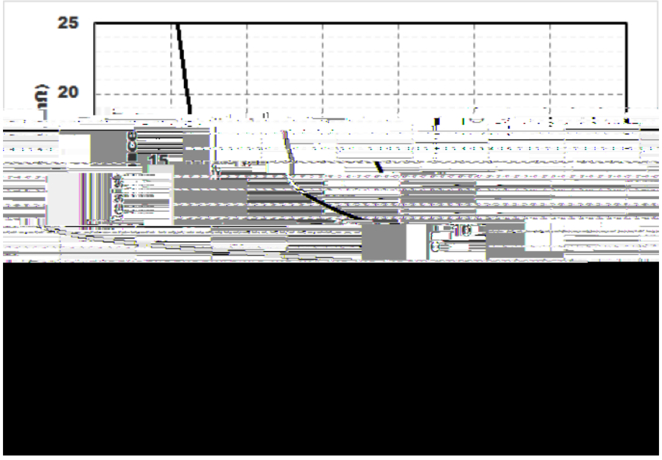


Figure5. : On-Resistance vs. Drain Current and Gate Voltage

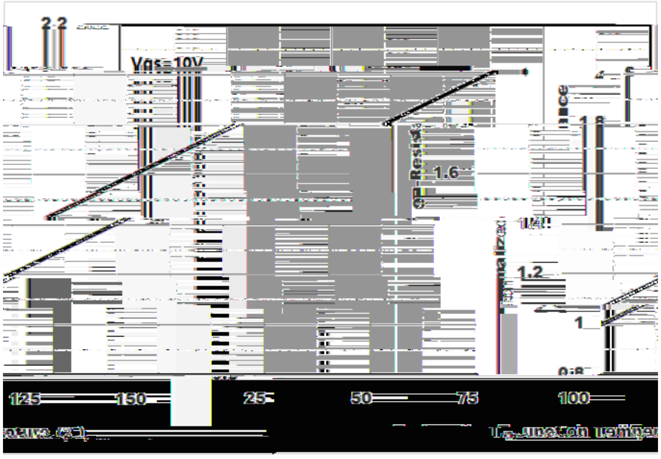
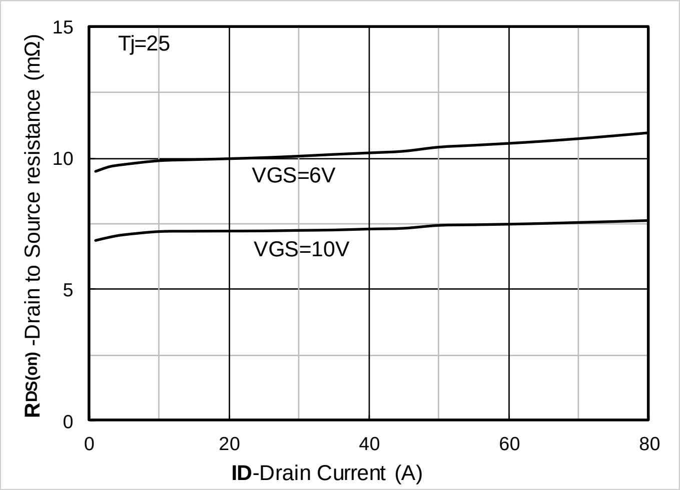


Figure6.Normalized On-Resistance



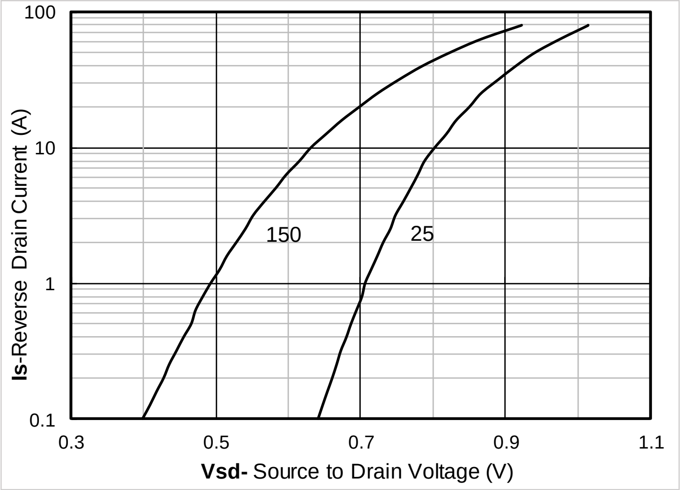
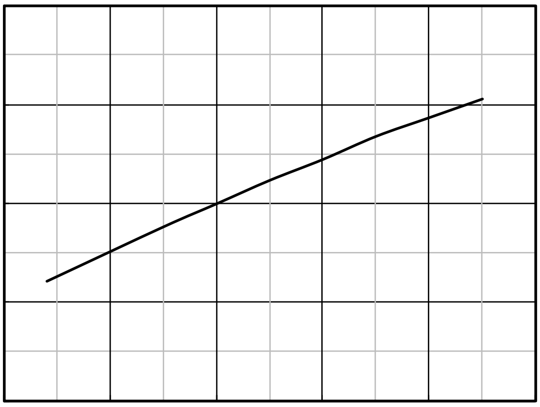


Figure 7. RDS(on) VS Drain Current

Figure 8. Forward characteristics of reverse diode



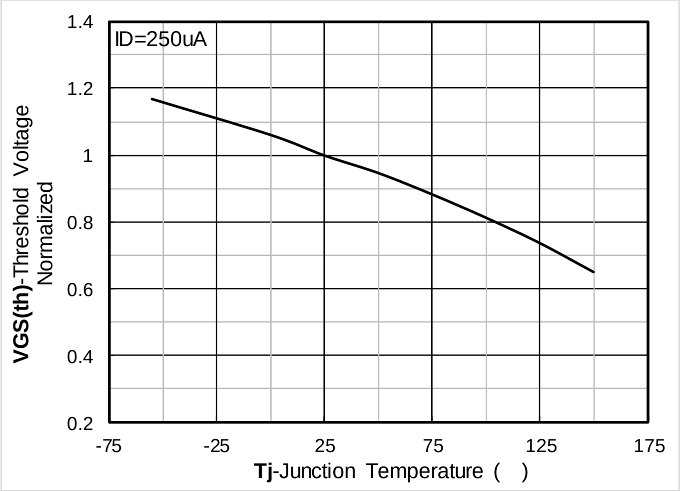


Figure 9. Normalized breakdown voltage

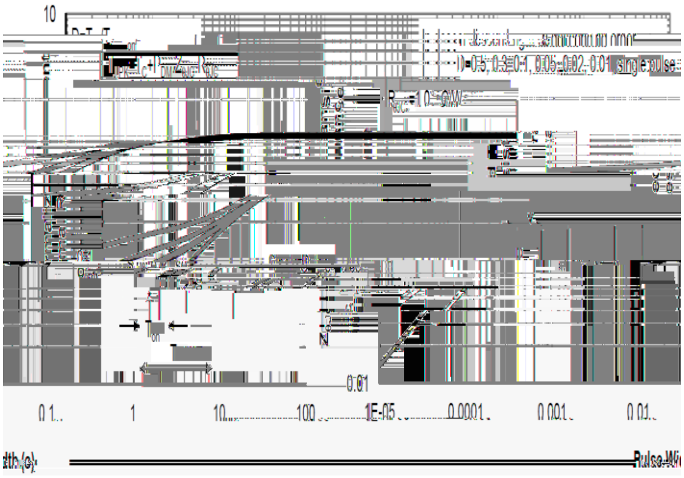


Figure 13. Normalized Maximum Transient thermal impedance

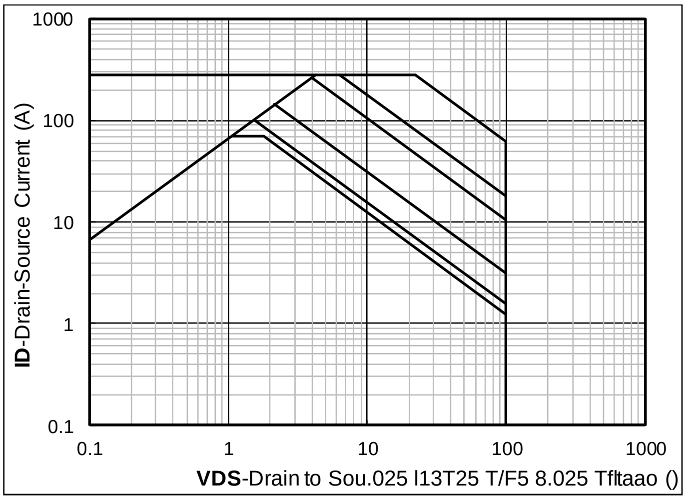


Figure 14. Safe Operation Area

■ TO-263-HY Package information

SYM.	MIN.	
A2		
b2		0.050
c		
c2		
D2		
E		
E1		

Disclaimer

The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise.

The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of with would directly endanger human life (such as